

Surface Electrode – Triangle – Ion Trap Technology Overview

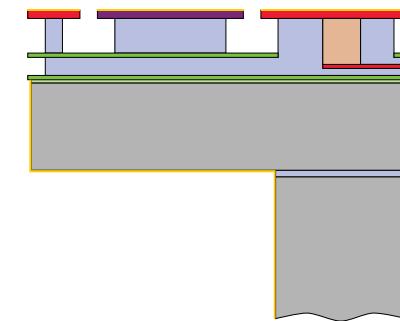
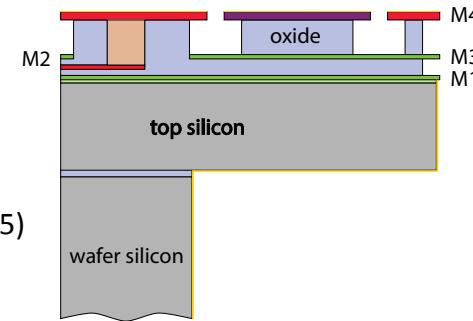
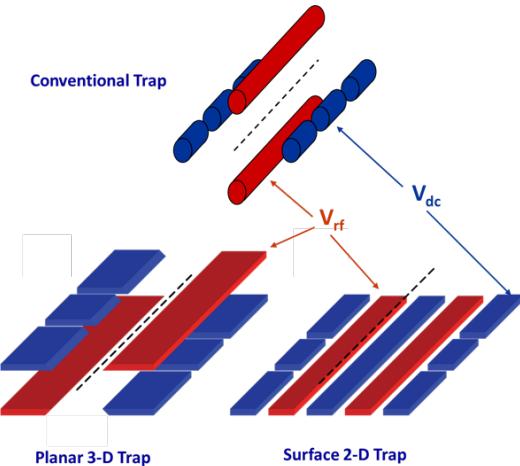
Matthew Blain
Daniel Stick

6 August 2013
NIST Boulder

Surface Electrode Ion Trap Fabrication

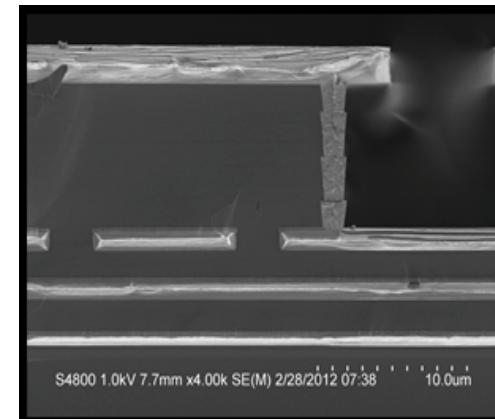


4-metal-layer process modified from Sandia 0.35 μ m Al/SiO₂ CMOS Process



J. Chiaverini, et al., Quant. Inf. Comp. 5, 419 (2005)

- 1.2/2.5 μ m Al 4LM technology
- Trap flow: ~300 ops, 11 mask levels used 17x
- Interposer flow: ~320 ops, 15 mask levels used 21x
- 10 μ m oxide separating RF(M4), ground (M3)
- Precision Chip thru-holes
- Release singulation
- Precisely recessed oxide
- Routing on M2
- Gold coating from front and back side





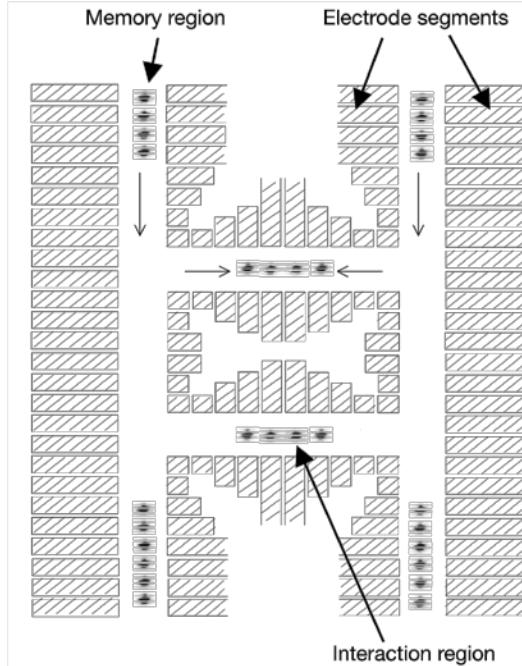
Possible geometries

multi-layer technology advantages

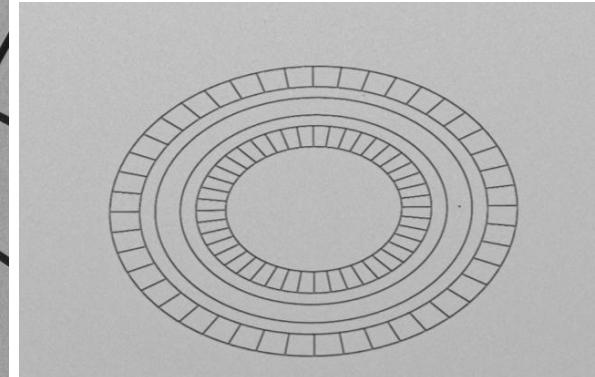
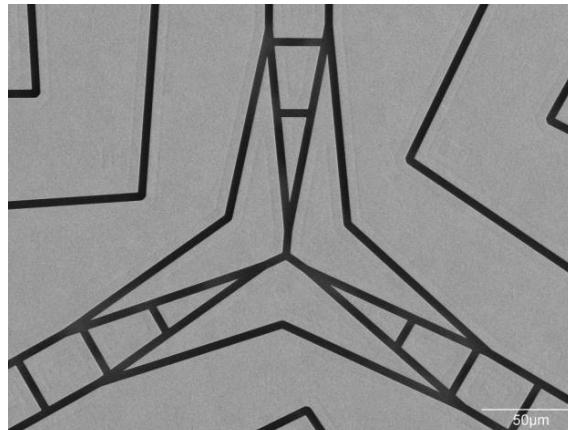
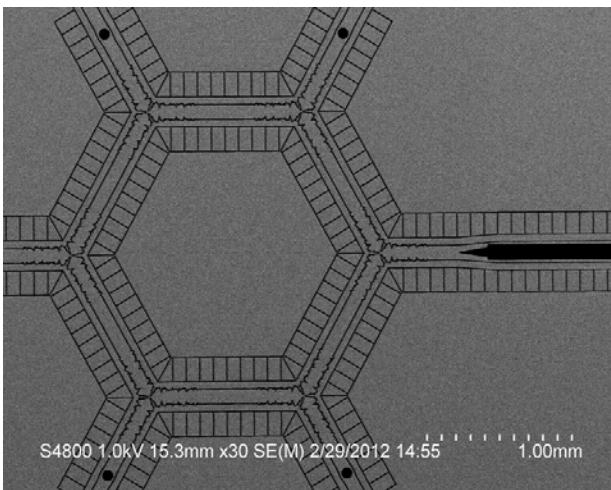
4-level-metal devices allow for:

- No exposed routing
- Islanded electrodes
- New topologies
- 5th layer for μ -wave delivery

Imagine your trap geometry:
it can be realized



D. Kielpinski, *et al.* Nature 417, 209 (2002).



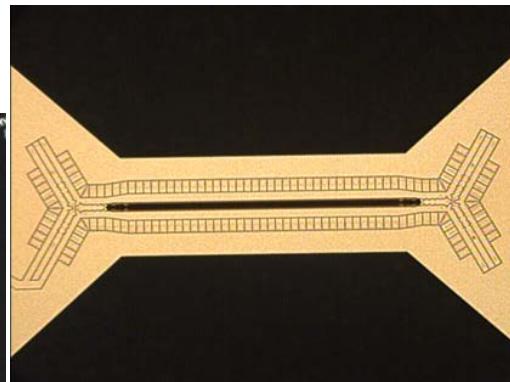
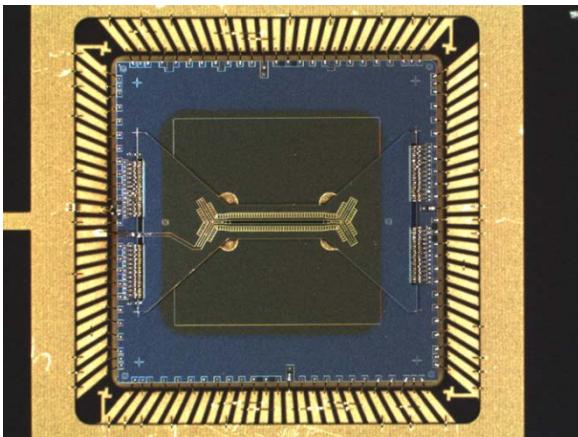
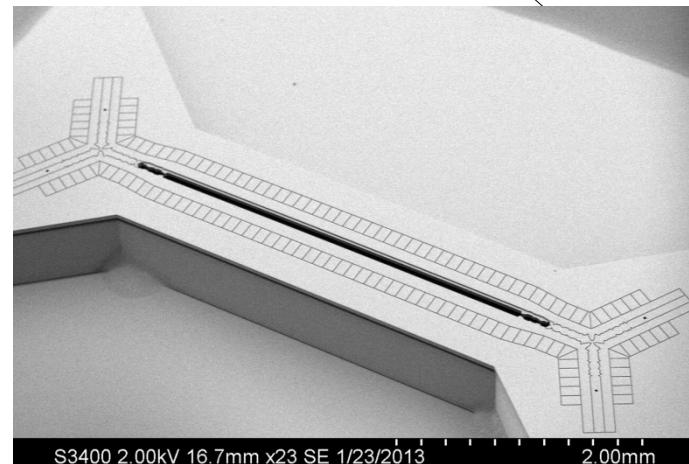
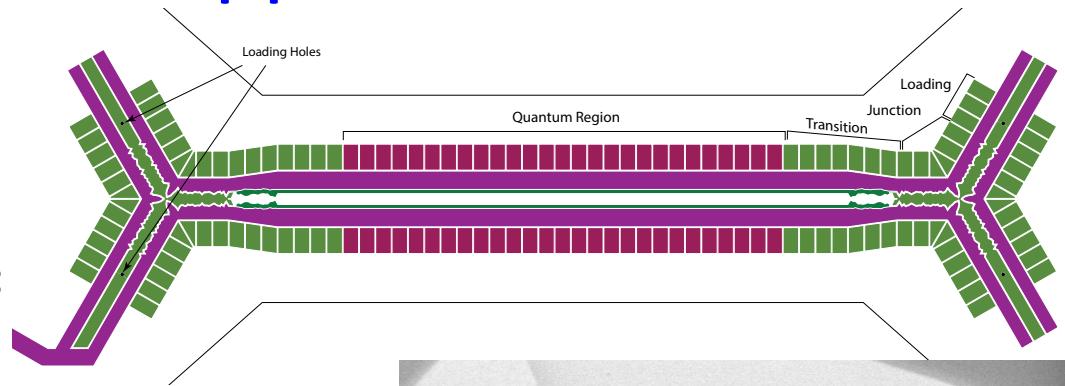


HOA trap platform

high optical access trap

Optimized surface electrode trap platform for QIP

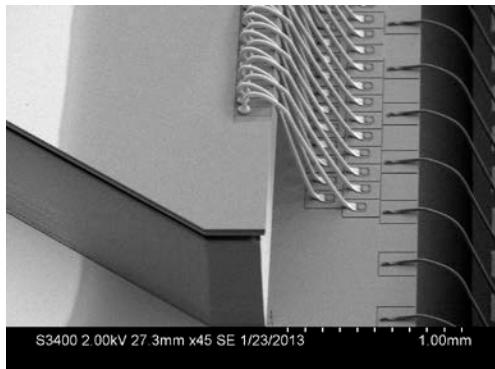
- Release singulation
- Unique shape
- Greatly improved optical access:
 - Larger trap depth
 - Higher trap frequencies
 - Less optical scatter



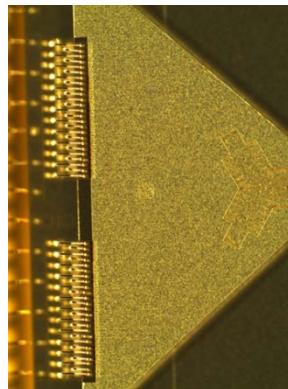


Interposers for Surface Traps

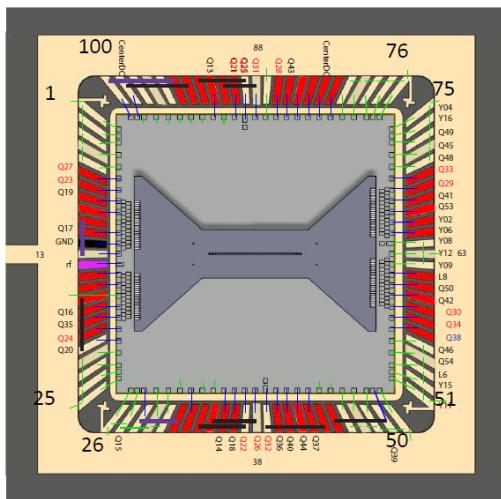
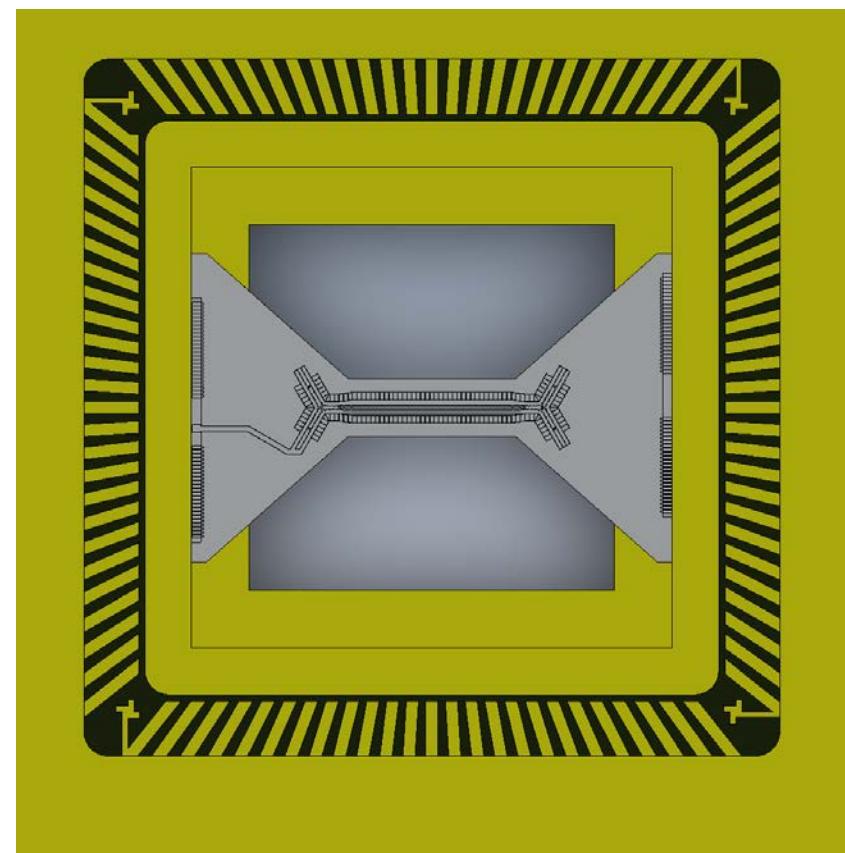
- Chip-to-interposer wires give unobstructed laser access to trapping region
- Redistribution layer (RDL) routes trap I/O (2-sides) to package (4-sides)



Sandia 48-pin chambers



Version 5

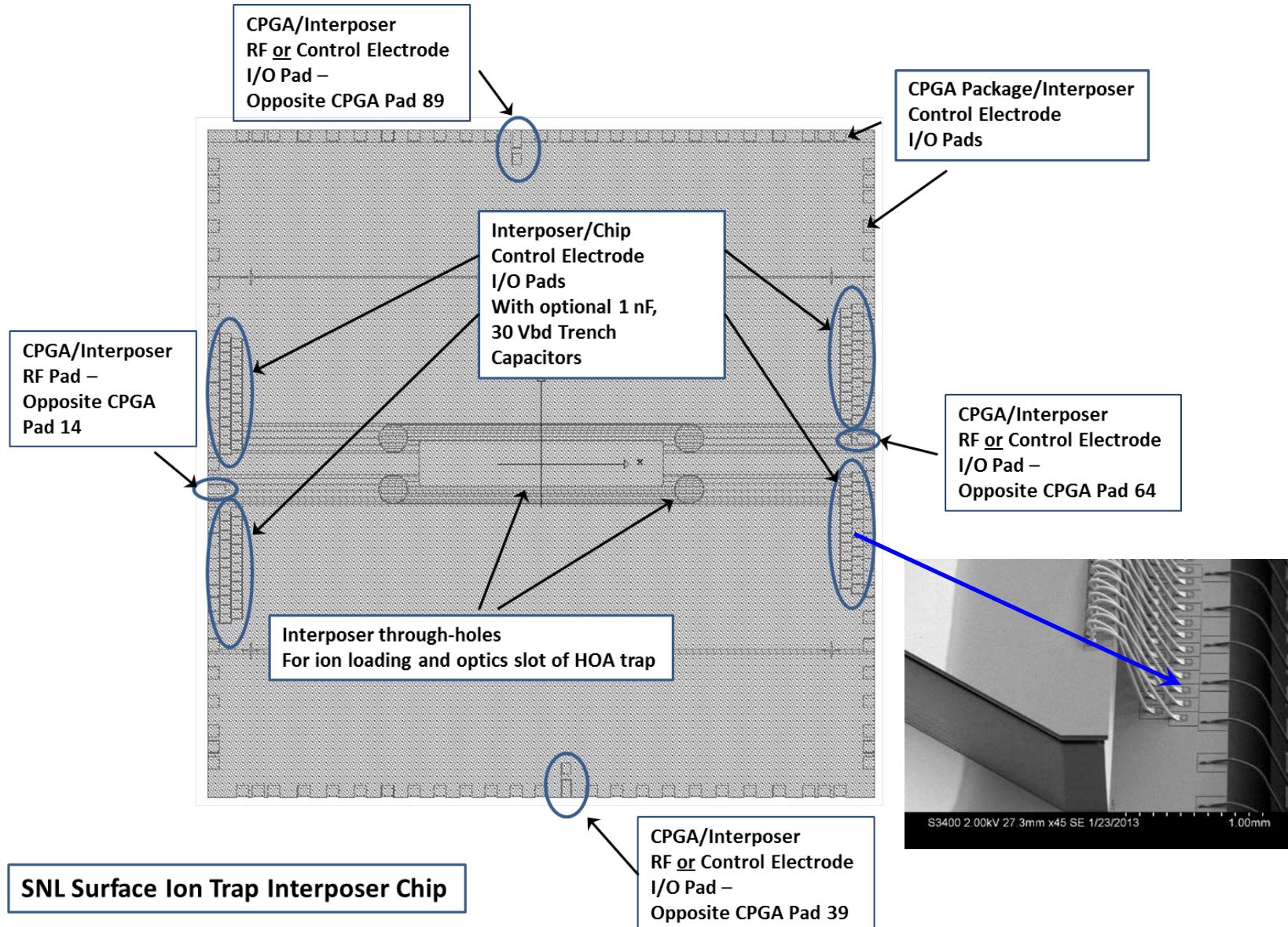


■ rf gnd
■ rf
■ Control
■ GND
■ Not used. The trap may short these pins to ground or to control pins.

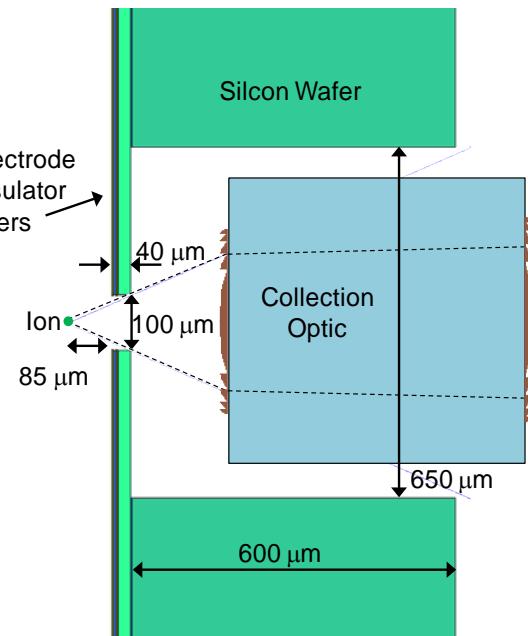
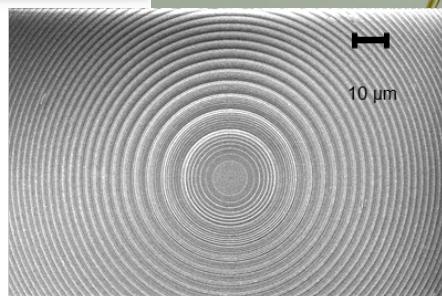
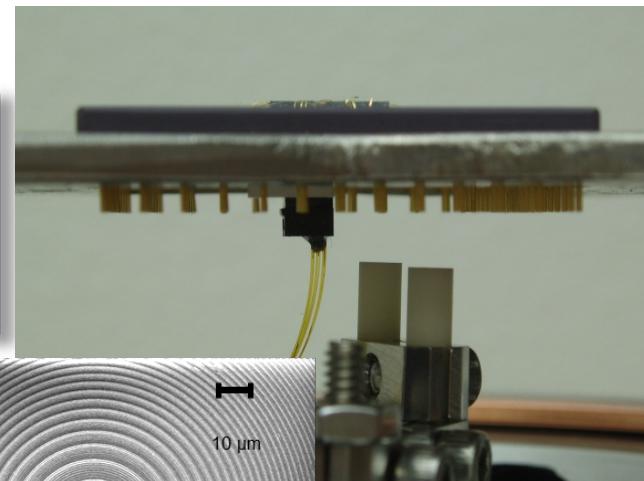
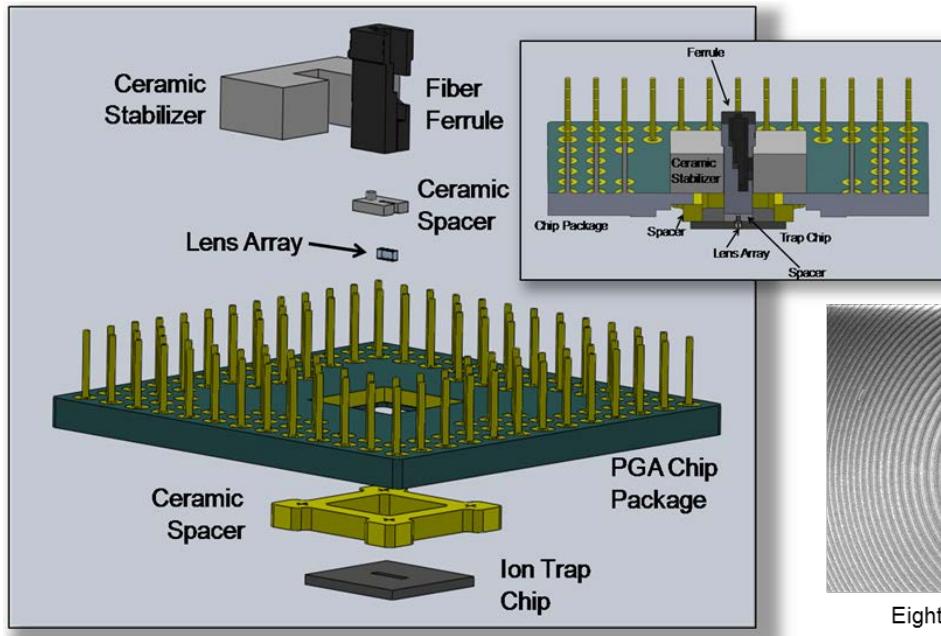
- Interposer can support:
 - Passive and active electronics
 - Future and (some) existing traps



Interposers for Surface Traps



Integrated Optics



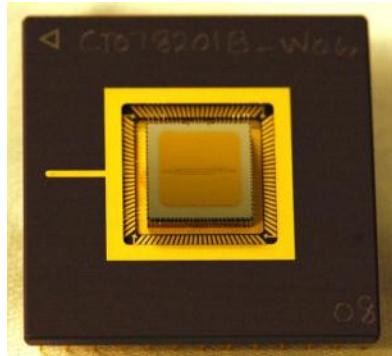
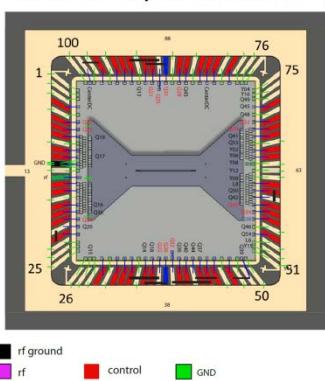
- Optics have been integrated into linear surface ion trap.
- No detrimental effects to ultra-high vacuum.
- Successful shuttling with same voltage solutions as linear trap without integrated optics.
- Compensated any charging on dielectric lenses.
- Dielectric lenses ~150 microns away from ion.

G. R. Brady, *et al.* Appl. Phys. B: Lasers and Optics 103, 801-808 (2011).

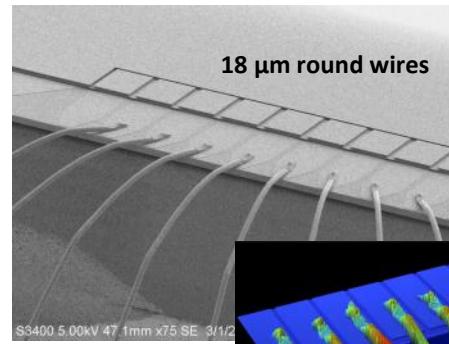
Packaging and testing

Plug-and-trap design

MQCO 48 pin chambers



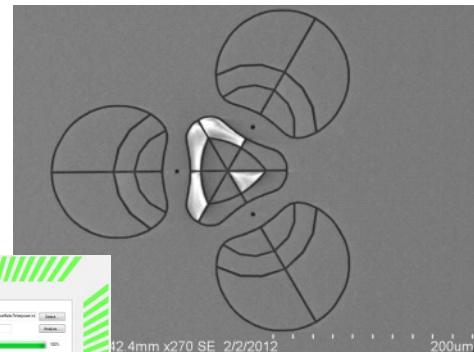
Low profile wirebonding



Plug-and-trap design

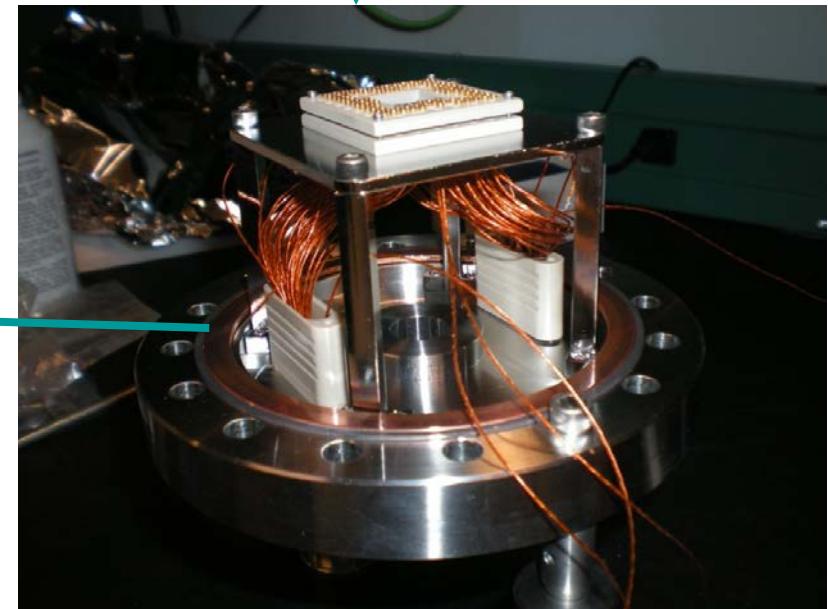
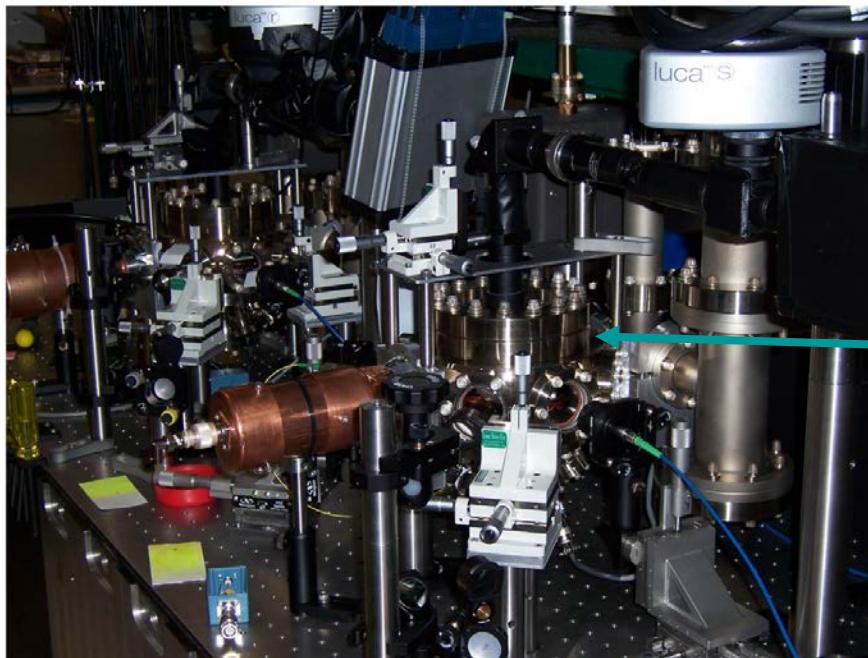
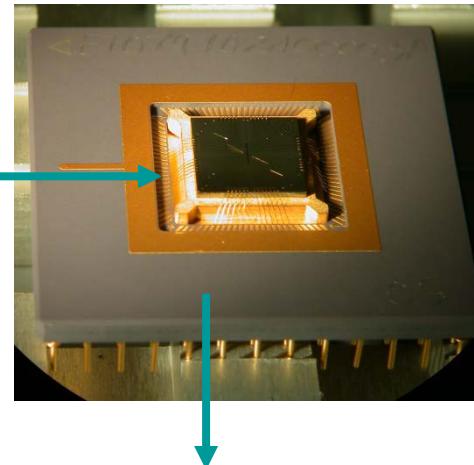
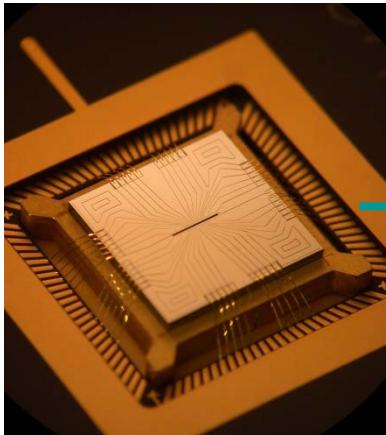
- Standard package part for chip ion traps
- Most trapping groups can accommodate the package
- Low profile wirebonds: good optical access
- Checks for opens and shorts > 40 MΩ

Parametric verification

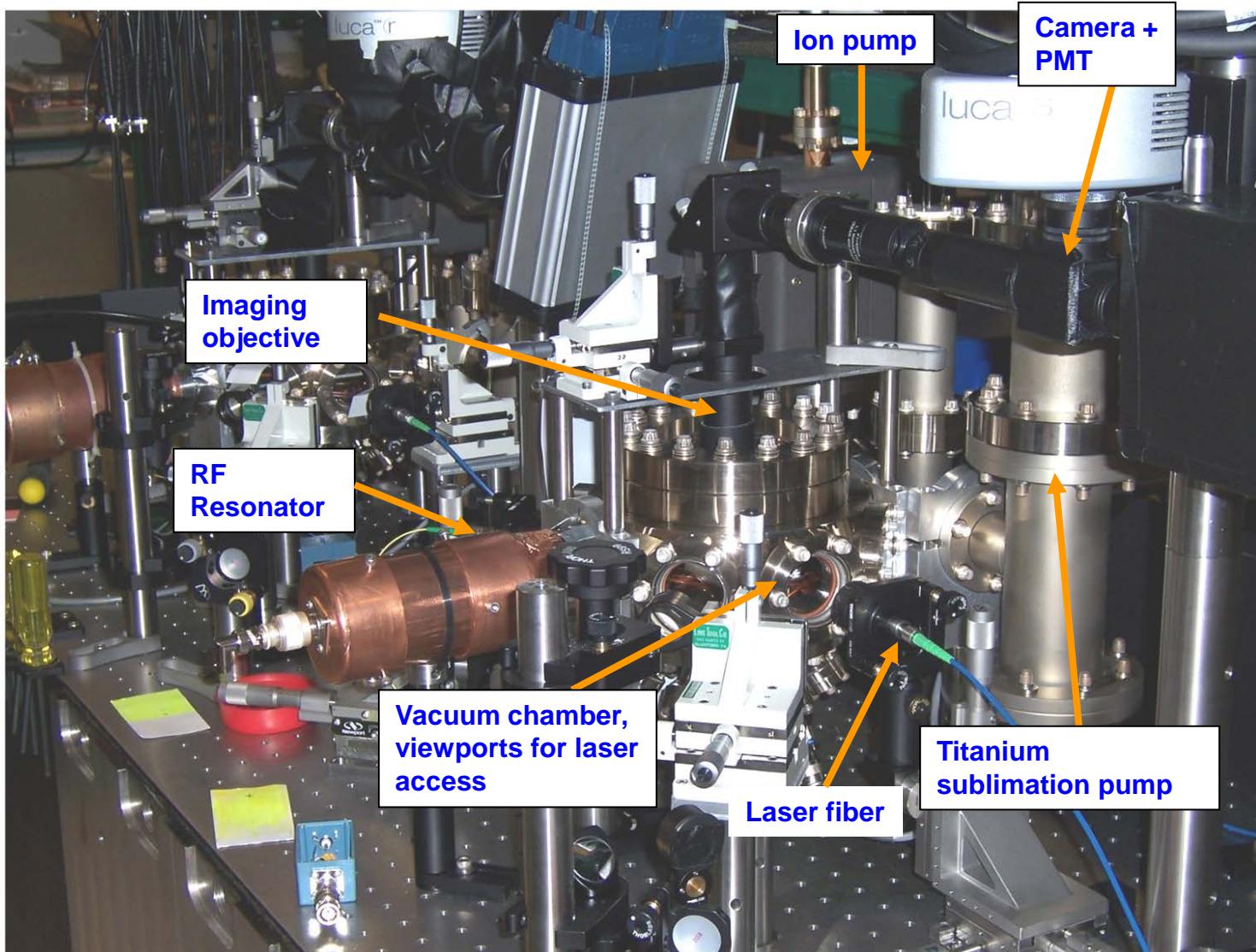


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Trap operational testing



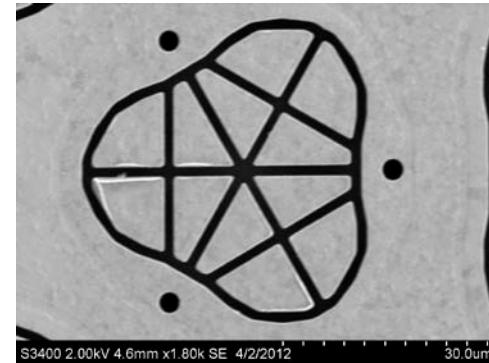
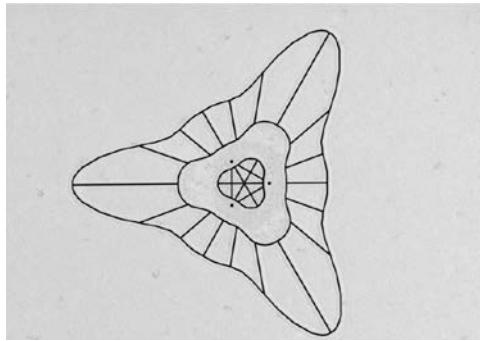
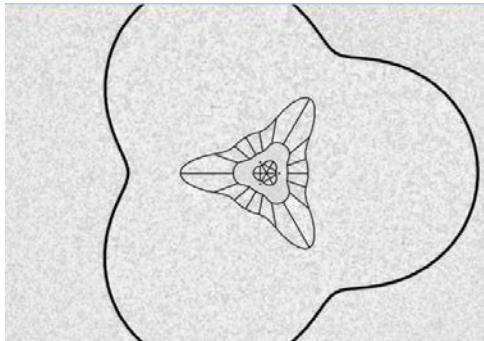
Trap operational testing



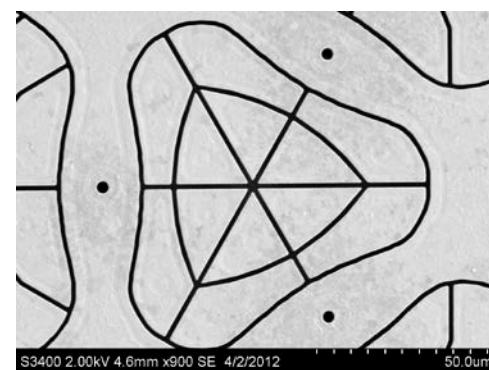
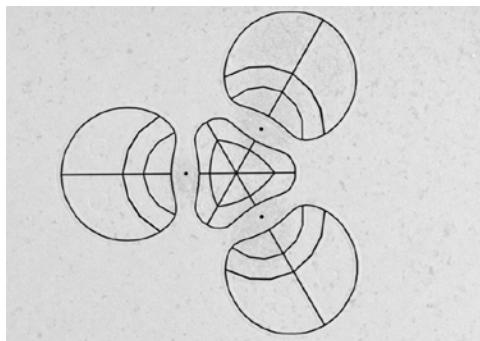
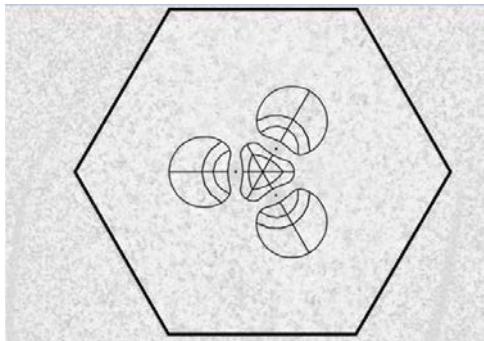
Triangle Trap Rev. 0 – 80 μm , 40 μm triangles



40 μm triangles



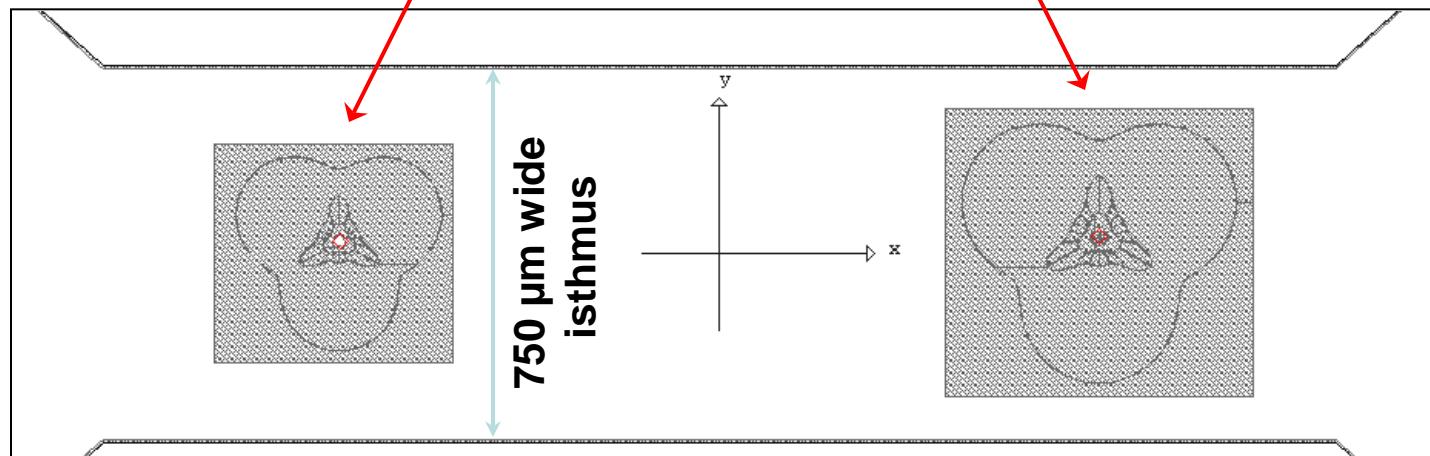
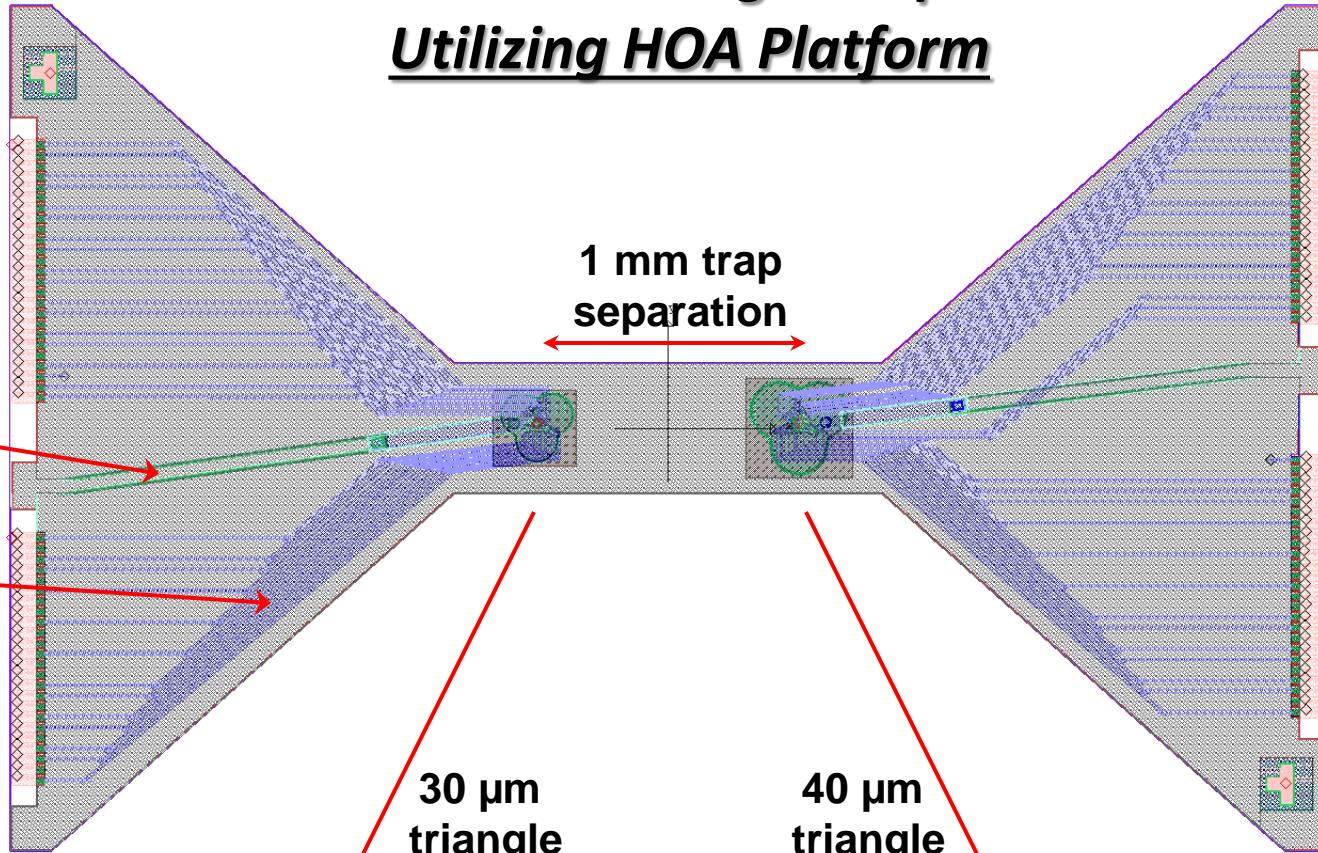
80 μm triangles





Revised Triangle Trap Utilizing HOA Platform

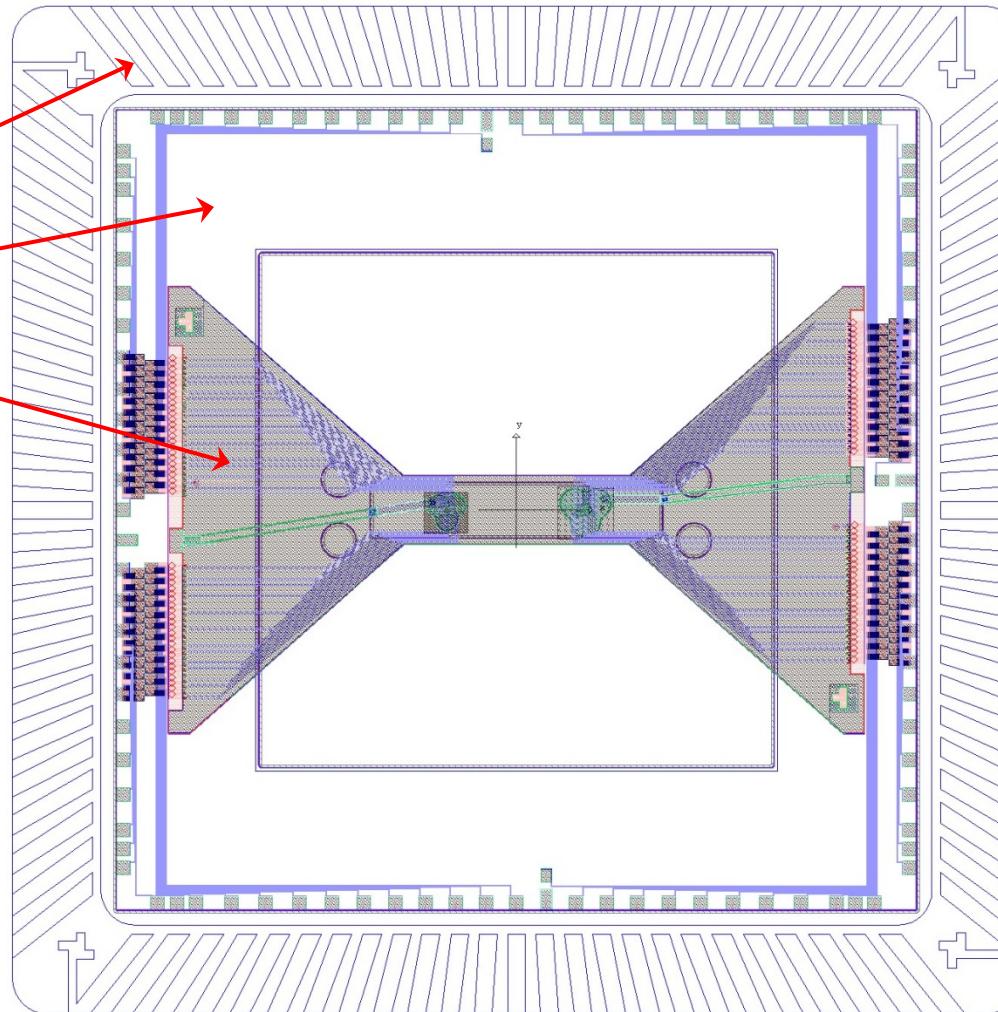
- Independent RF leads
- Independent DC controls





Revised Triangle Trap Packaging Design

- Package
- Interposer
- Trap Chip



Trap Status

Triangle Trap

- Utilize existing 40 μm triangle design
- Add scaled 30 μm triangle design
- Layout complete August 2013
- Photomasks ordered, lot start September 2013
- Device fabrication/packaging completed March 2014

Hex + 1 Trap

- Simulate/design Hex + 1 4LM surface electrode trap utilizing concepts of hexagonal Kitaev trap array (Didi to discuss)
- Perform device layout for Hex + 1 ion trap
 - Independent control for 4 ions in Y configuration



I A R P A

Surface Electrode Ion Trap Technology Overview



Sandia
National
Laboratories

Matthew Blain – Org. 1725

6 August 2013

Experimental

D. Stick
P. Maunz
K. Fortier
D. Sterk
C. Tigges
B. Tabakov
F. Benito
T. Barrick
C. Johnson



Ion Traps

M. Blain
B. Loviza
A. Ortega
E. Heller
R. Haltli
D. Hollowell
L. Fang
J. Gallegos

Micro-Optics

S. Kemme
R. Ellis
R. Boye
A. Young
S. Samora

MESA Staff:
→SiFab/μFab



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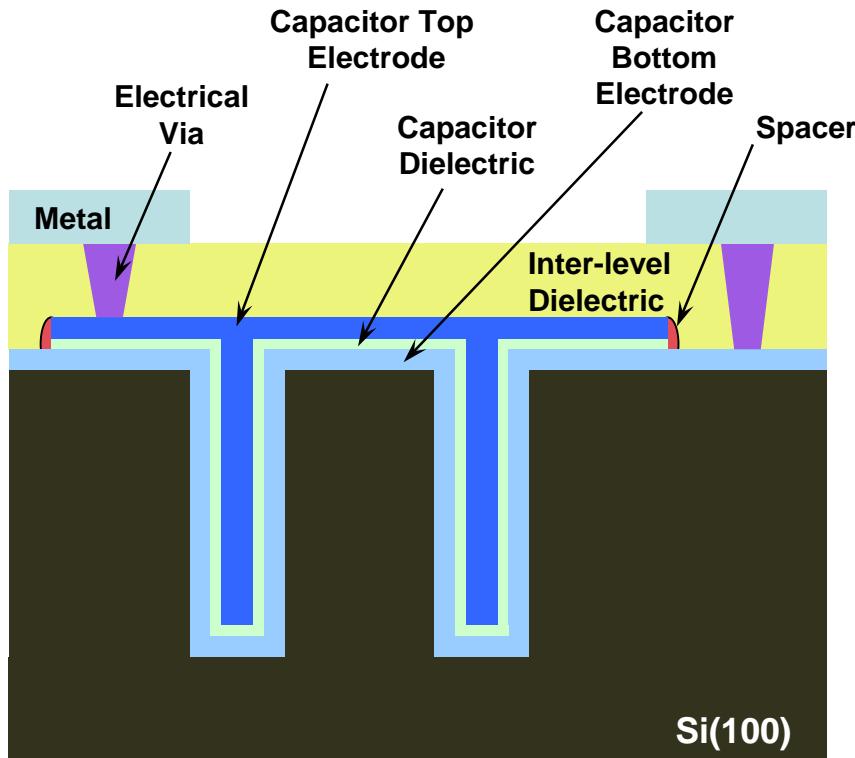


Integrated Trench Capacitors

Trench v. Surface Capacitors for Surface Ion Traps

- High-k dielectric surface areas: still large
- Thin dielectric challenges: yield, reliability
- Vertical surfaces: more available area

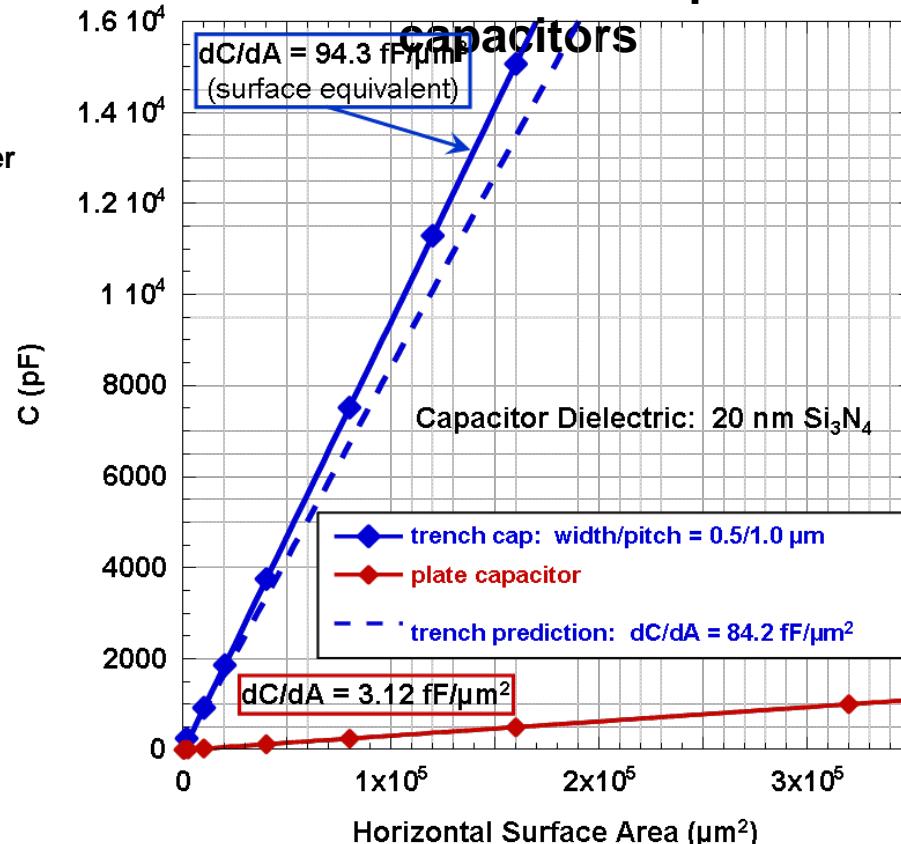
Trench Capacitor Architecture



ATC 116 Series Microcaps

Surface mount: $1.27 \times 1.27 \text{ mm}^2$, $821 \pm 20\% \text{ pF}$

Area relationship for trench v. horizontal plate capacitors

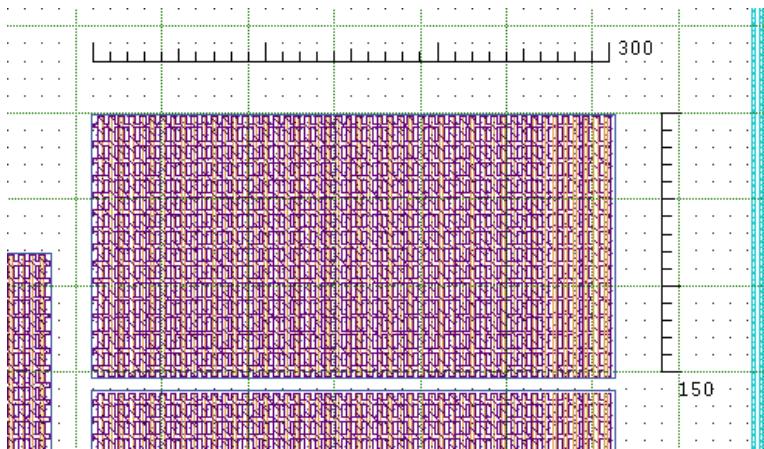




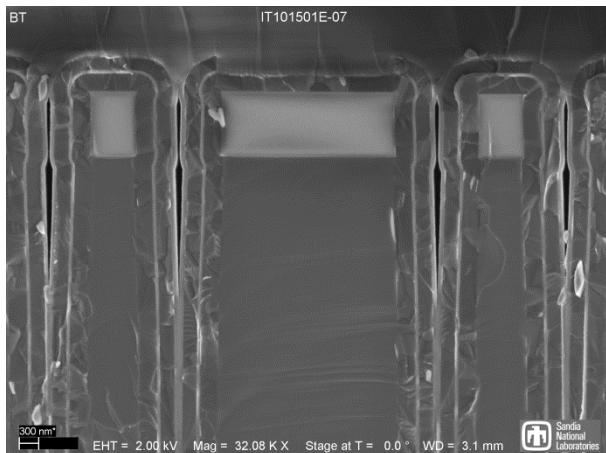
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Integrated Trench Capacitors

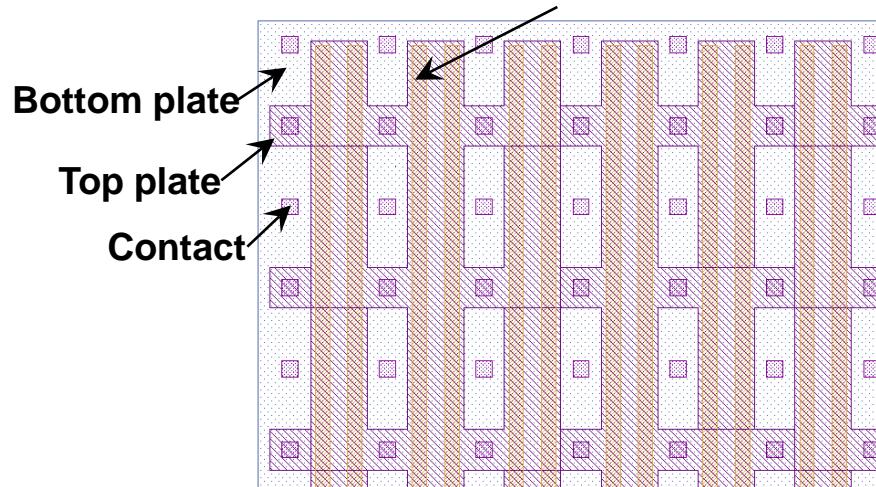
1.05 nF trench cap, 0.045 mm²/cap



Top plate: 250 nm n-type a-Si
Dielectric: 40 nm Si₃N₄
Bottom plate: 300 nm n-type a-Si



Trenches: 1 μm wide, 150 μm long, 19 μm deep



19 μm

